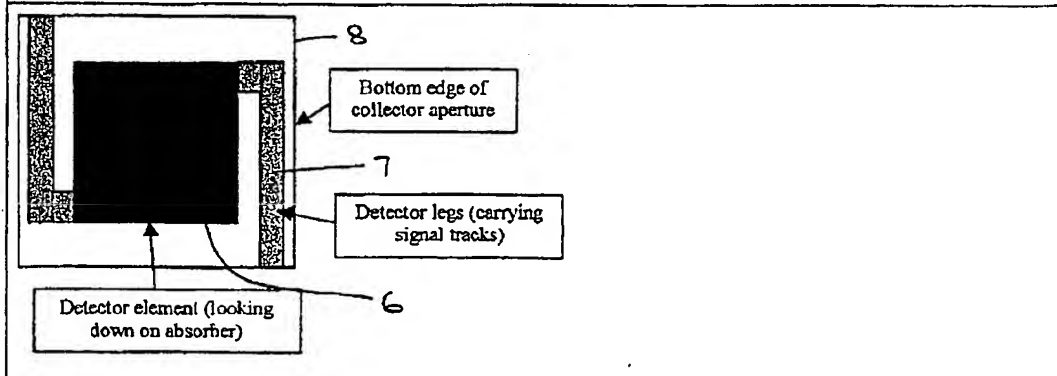
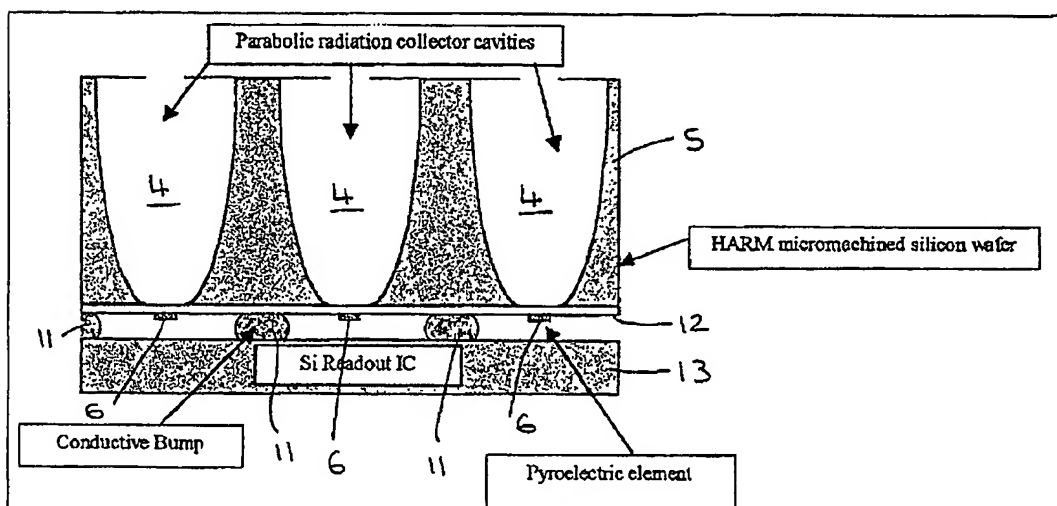
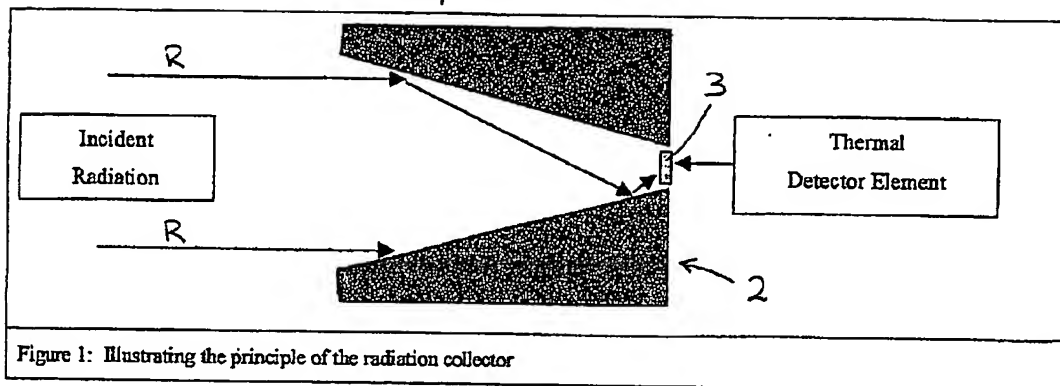
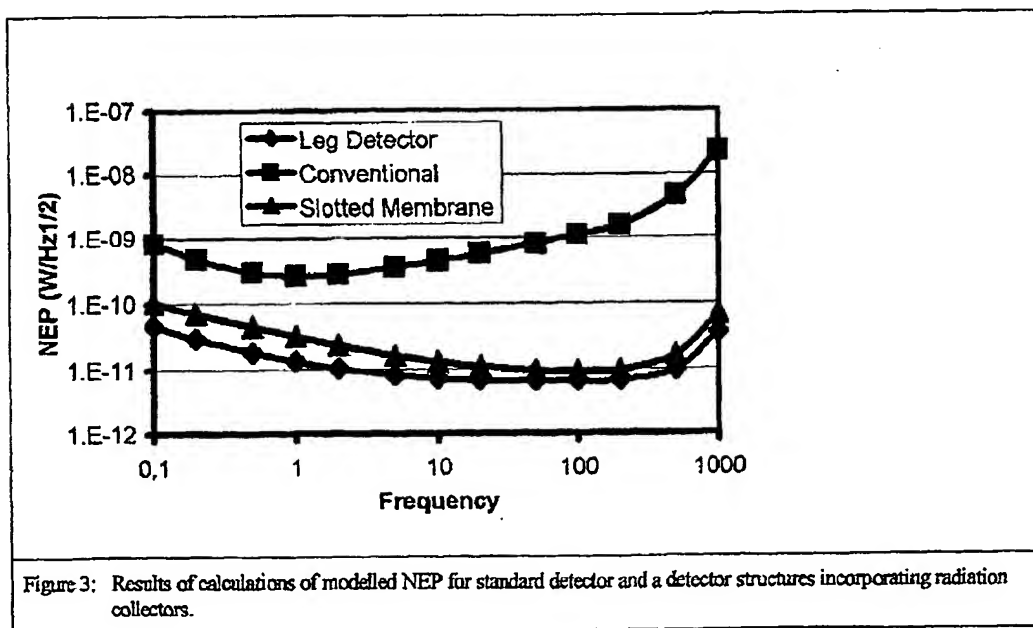
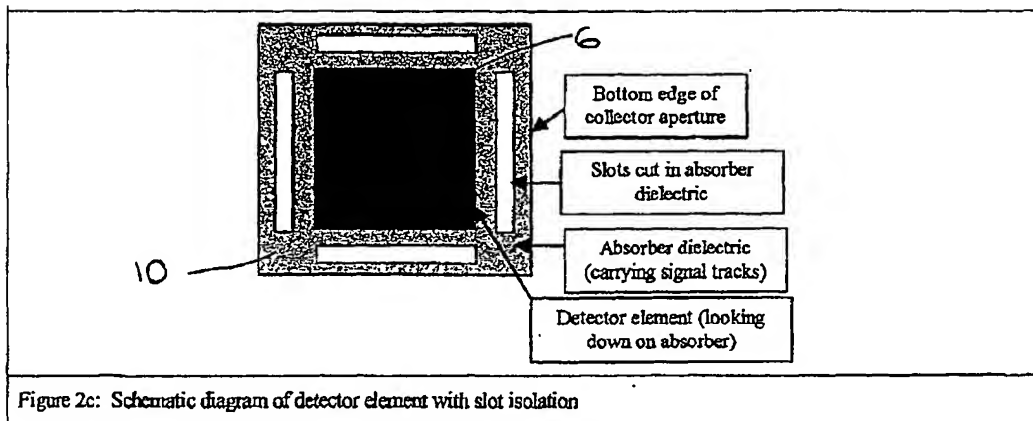


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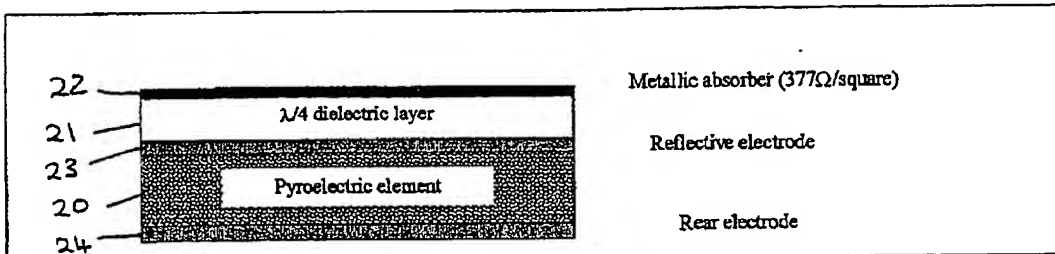


Figure 4a: Dielectric absorber layer (1.7μm SiO₂)

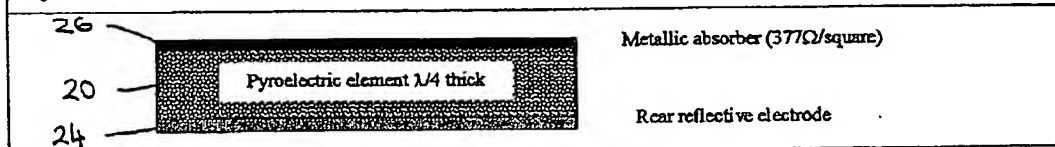


Figure 4b: Pyroelectric thin film as the absorber layer.

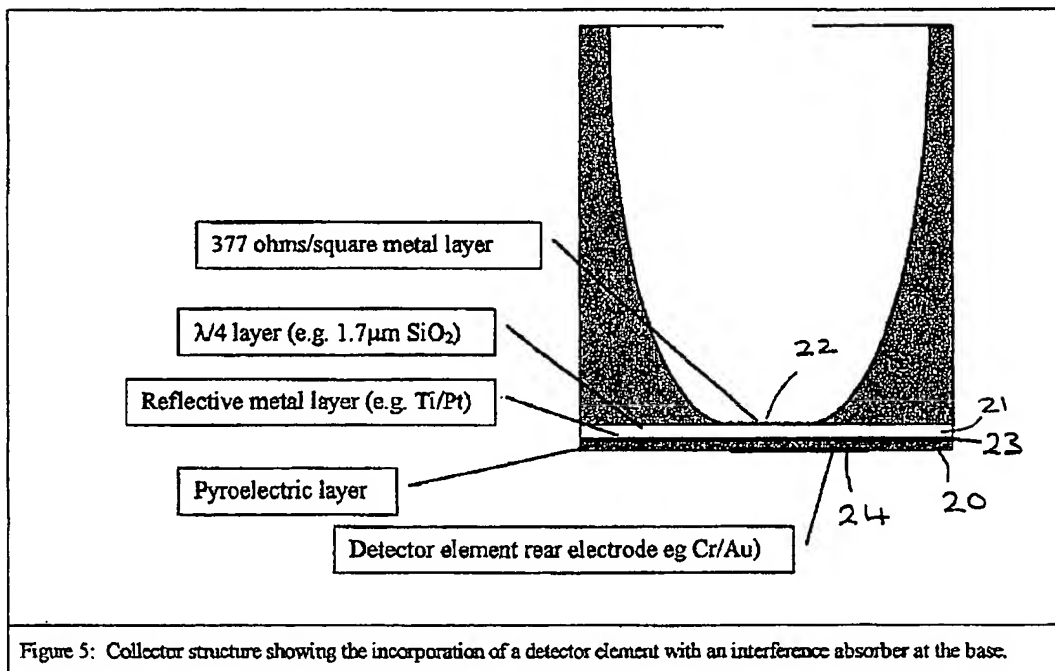


Figure 5: Collector structure showing the incorporation of a detector element with an interference absorber at the base.

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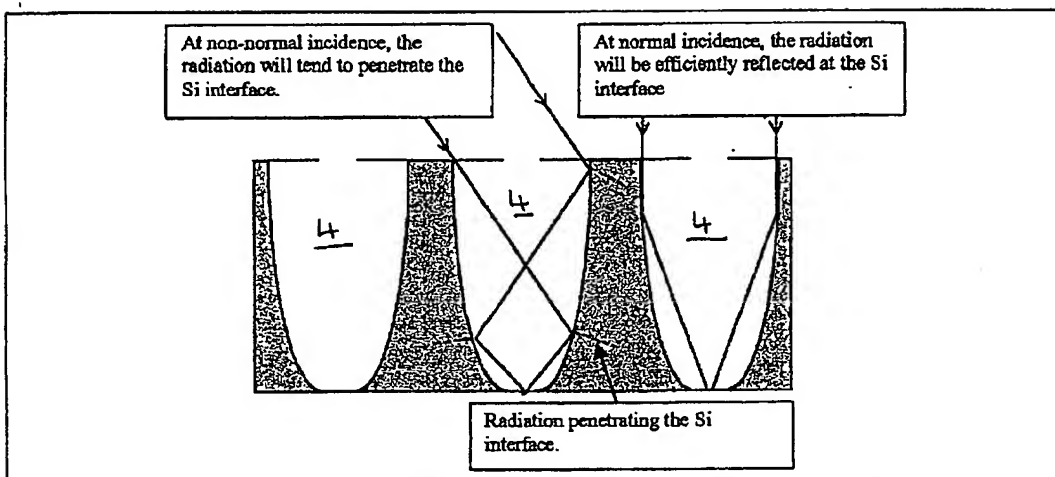


Figure 6a: Illustrating the effects of signal loss for non-normal incidence radiation.

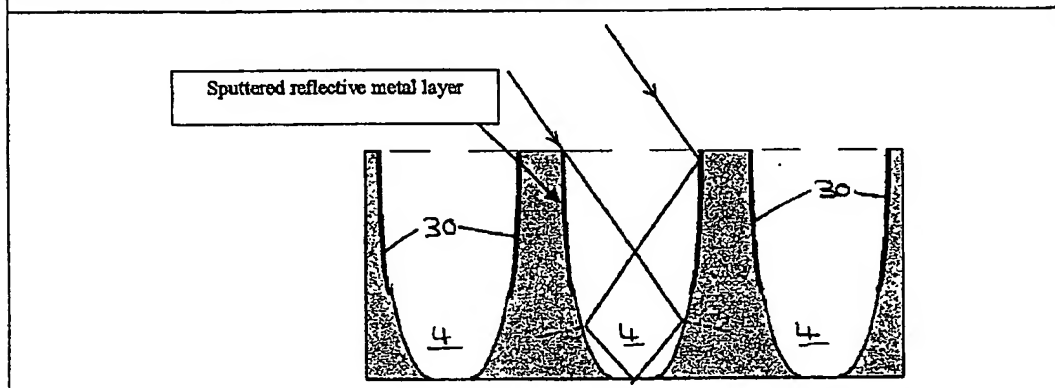


Figure 6b: Coating the upper regions of the reflector array will tend to allow the radiation to be reflected deeper into the collector cavity.

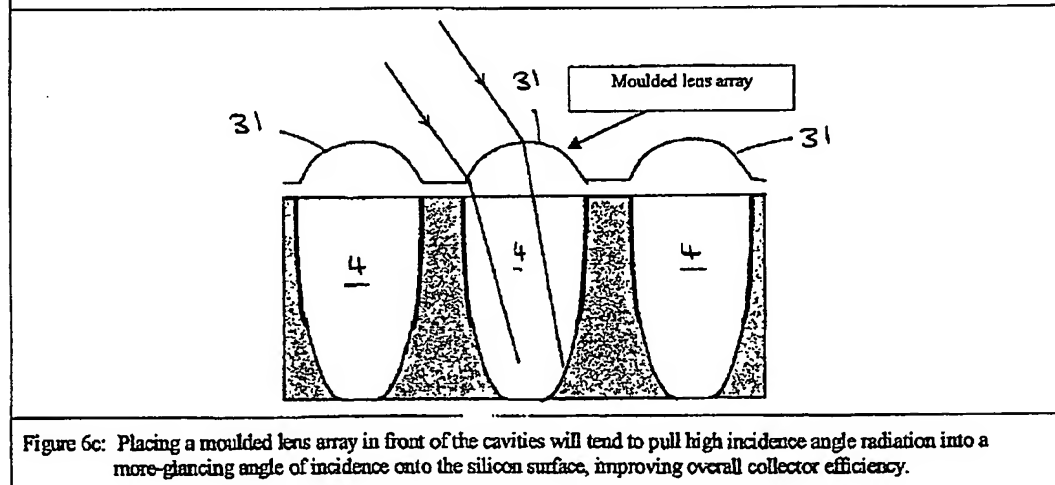


Figure 6c: Placing a moulded lens array in front of the cavities will tend to pull high incidence angle radiation into a more-glancing angle of incidence onto the silicon surface, improving overall collector efficiency.

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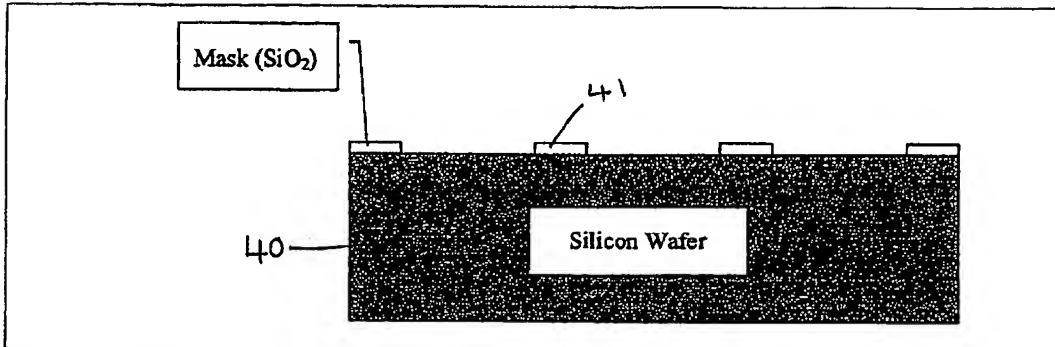


Figure 7a: Silicon wafer with "hard" mask defined

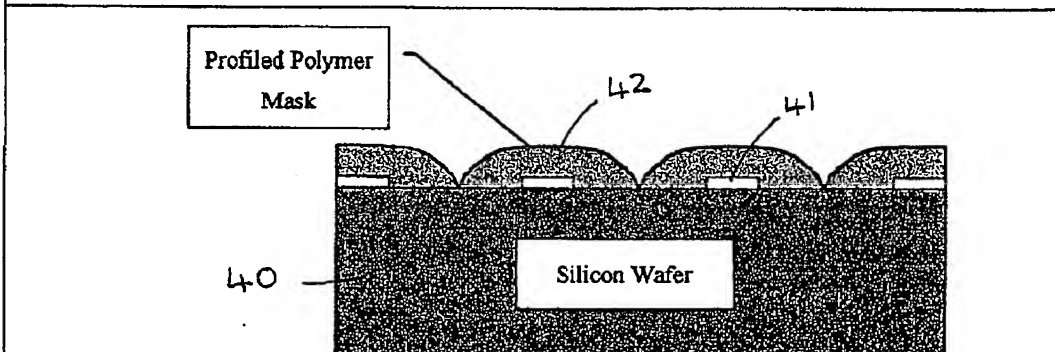


Figure 7b: Silicon wafer with profiled polymer mask defined

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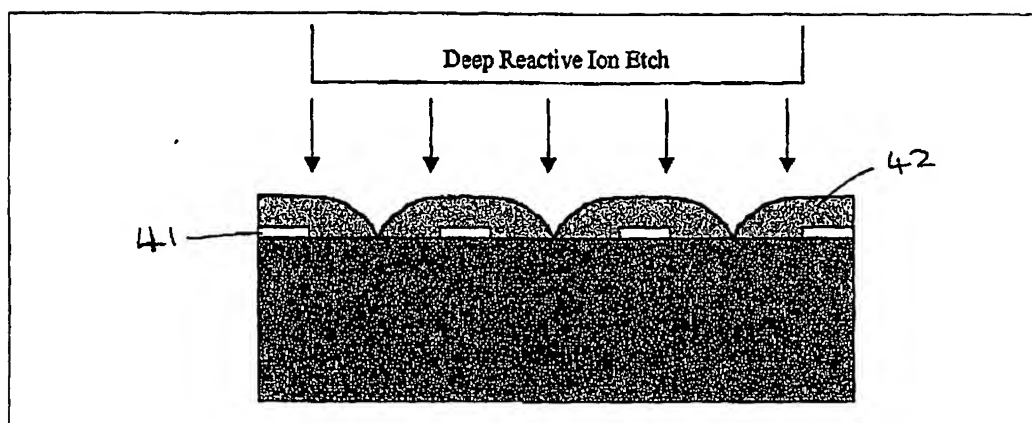


Figure 7c: Silicon wafer with masks exposed to DRIE

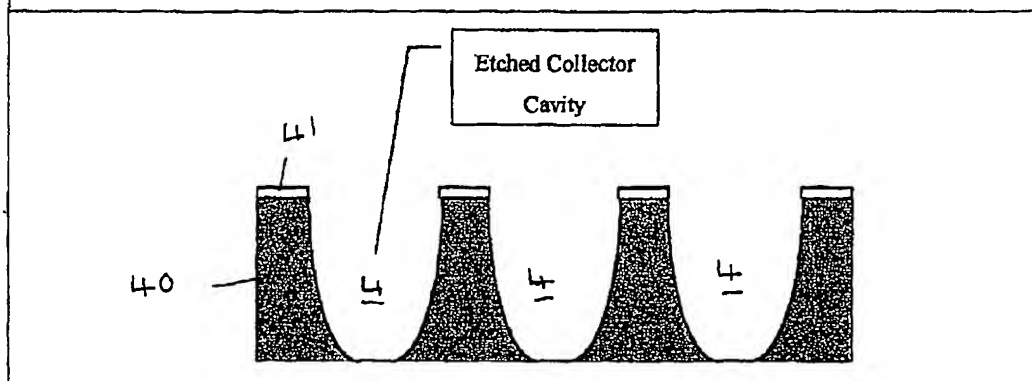


Figure 7d: Silicon wafer with cavities etched by DRIE